

# FDP52N20 / FDPF52N20T

## N-Channel MOSFET

200V, 52A, 0.049Ω

### Features

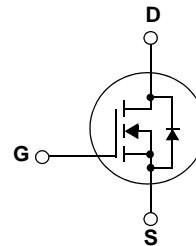
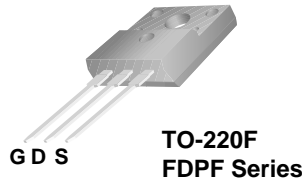
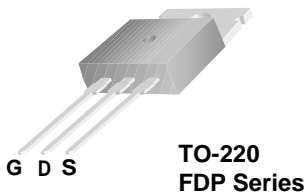
- $R_{DS(on)} = 0.041\Omega$  (Typ.) @  $V_{GS} = 10V, I_D = 26A$
- Low gate charge (Typ. 49nC)
- Low  $C_{rss}$  (Typ. 66pF)
- Fast switching
- 100% avalanche tested
- Improve dv/dt capability
- RoHS compliant



### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advance technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switching mode power supplies and active power factor correction.



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDP52N20	FDPF52N20T	Units
$V_{DSS}$	Drain to Source Voltage	200		V
$V_{GSS}$	Gate to Source Voltage	±30		V
$I_D$	Drain Current	-Continuous ( $T_C = 25^\circ\text{C}$ )	52	52*
		-Continuous ( $T_C = 100^\circ\text{C}$ )	33	33*
$I_{DM}$	Drain Current	- Pulsed (Note 1)	208	208*
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	2520		mJ
$I_{AR}$	Avalanche Current (Note 1)	52		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	35.7		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	357	38.5
		- Derate above $25^\circ\text{C}$	2.86	0.3
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

\*Drain current limited by maximum junction temperature

### Thermal Characteristics

Symbol	Parameter	FDP52N20	FDPF52N20T	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	3.3	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	-	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	

**Package Marking and Ordering Information**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP52N20	FDP52N20	TO-220	-	-	50
FDPF52N20T	FDPF52N20T	TO-220F	-	-	50

**Electrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	200	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.2	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{V}, V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 160\text{V}, T_C = 125^\circ\text{C}$	-	-	10	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 26\text{A}$	-	0.041	0.049	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{V}, I_D = 26\text{A}$ (Note 4)	-	35	-	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	2230	2900	pF
$C_{oss}$	Output Capacitance		-	540	700	pF
$C_{rss}$	Reverse Transfer Capacitance		-	66	100	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 160\text{V}, I_D = 52\text{A}$ $V_{GS} = 10\text{V}$ (Note 4, 5)	-	49	63	nC
$Q_{gs}$	Gate to Source Gate Charge		-	19	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	24	-	nC

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{V}, I_D = 20\text{A}$ $R_G = 25\Omega$ (Note 4, 5)	-	53	115	ns
$t_r$	Turn-On Rise Time		-	175	359	ns
$t_{d(off)}$	Turn-Off Delay Time		-	48	107	ns
$t_f$	Turn-Off Fall Time		-	29	68	ns

**Drain-Source Diode Characteristics**

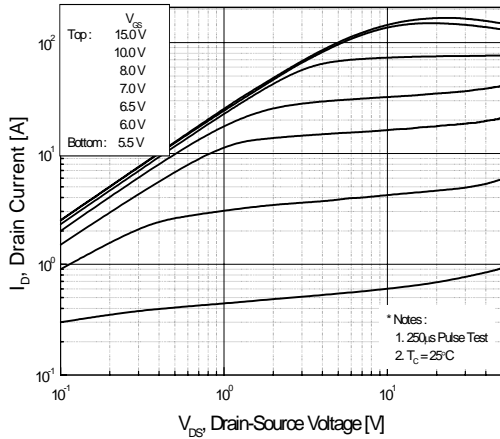
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	52	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	204	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 52\text{A}$	-	-	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_{SD} = 52\text{A}$	-	162	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	1.3	-	$\mu\text{C}$

**Notes:**

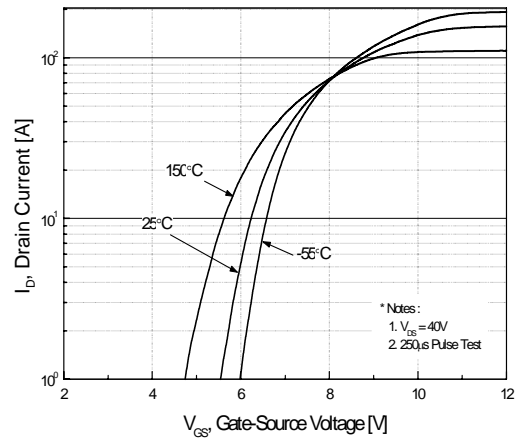
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 1.4\text{mH}, I_{AS} = 52\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 52\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

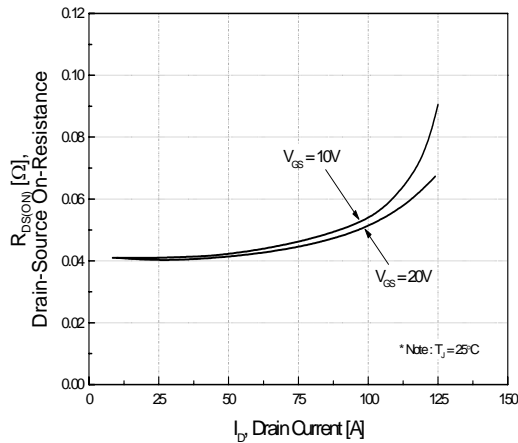
**Figure 1. On-Region Characteristics**



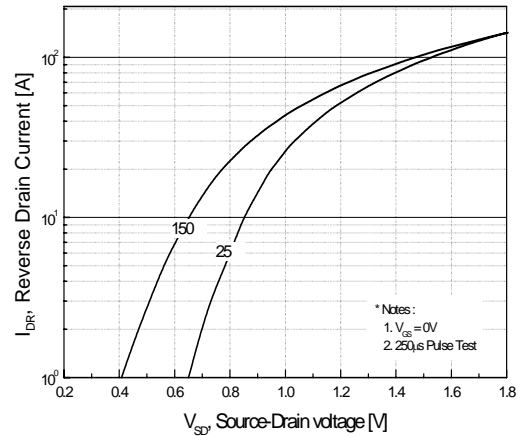
**Figure 2. Transfer Characteristics**



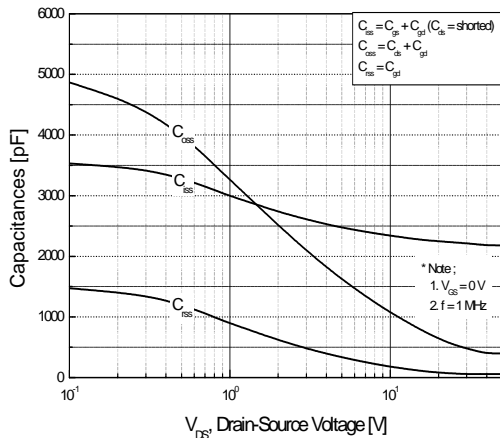
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



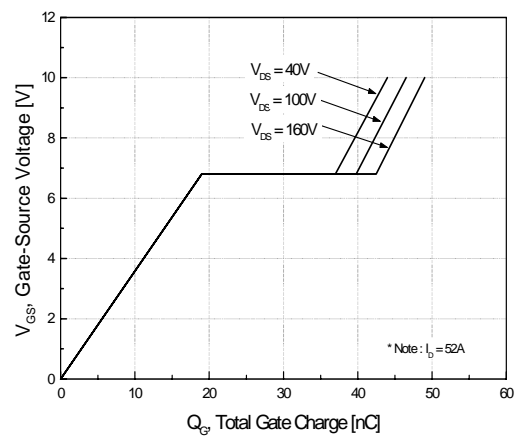
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

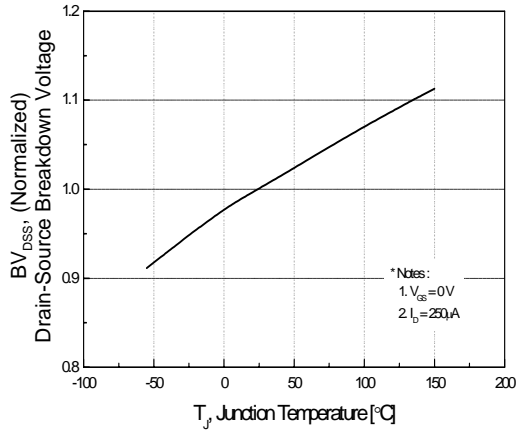


**Figure 6. Gate Charge Characteristics**

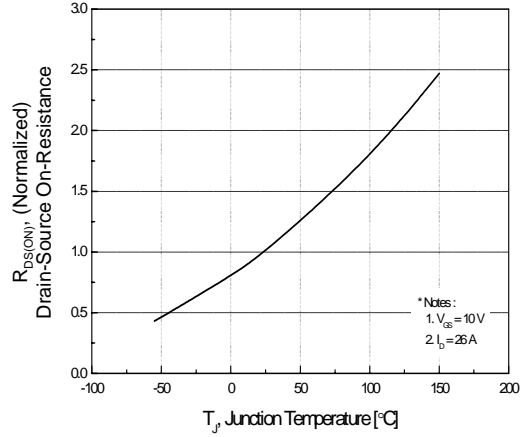


**Typical Performance Characteristics** (Continued)

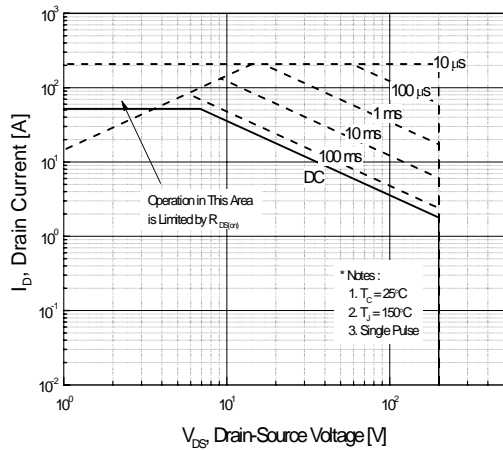
**Figure 7. Breakdown Voltage Variation vs. Temperature**



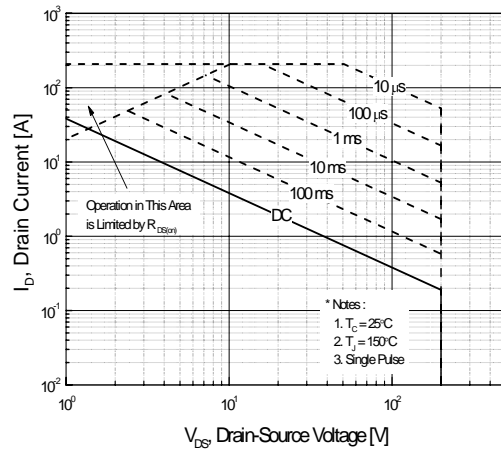
**Figure 8. On-Resistance Variation vs. Temperature**



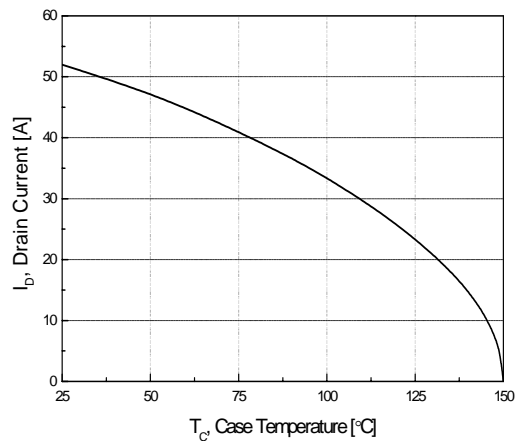
**Figure 9-1. Maximum Safe Operating Area - FDP52N20**



**Figure 9-2. Maximum Safe Operating Area - FDPF52N20T**

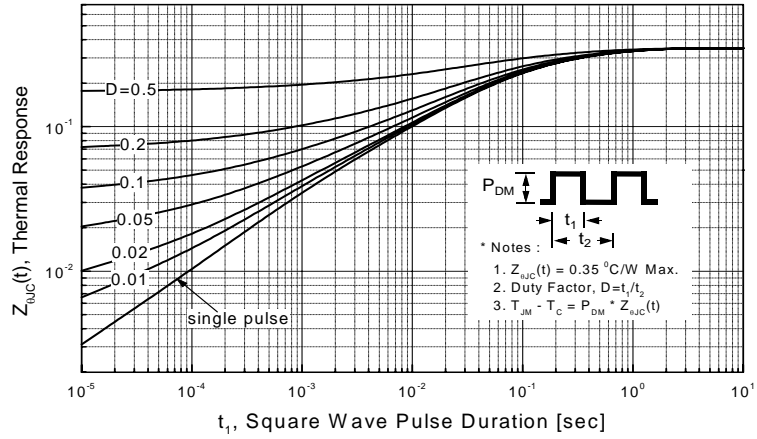


**Figure 10. Maximum Drain Current**

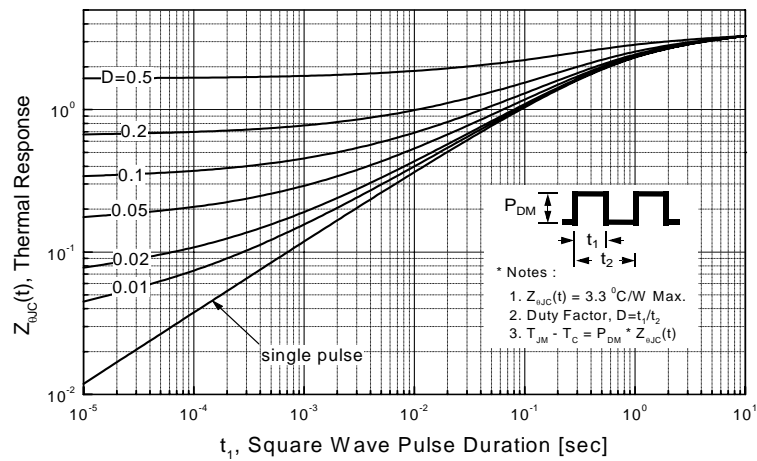


**Typical Performance Characteristics** (Continued)

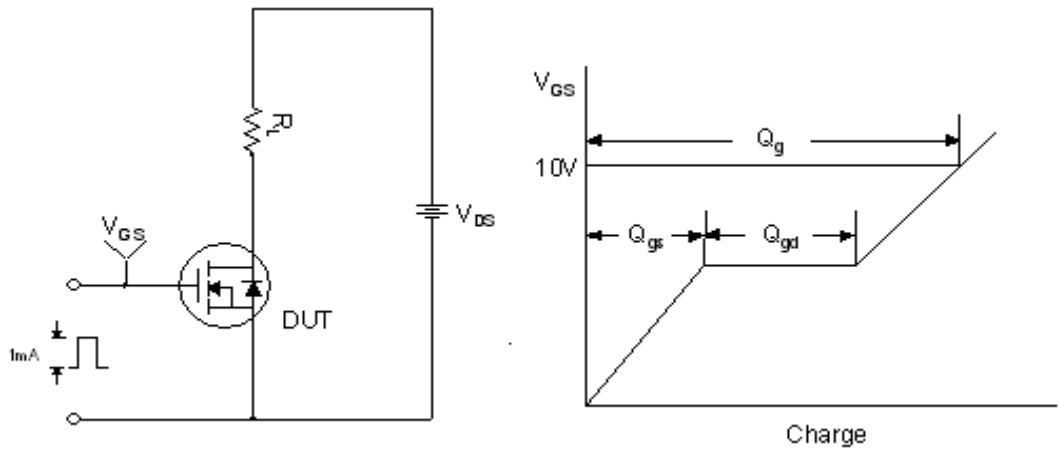
**Figure 11-1. Transient Thermal Response Curve - FDP52N20**



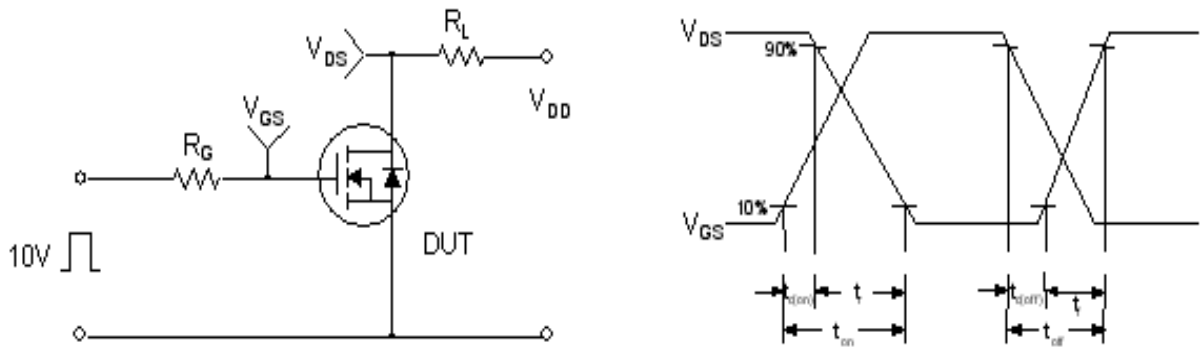
**Figure 11-2. Transient Thermal Response Curve - FDPF52N20T**



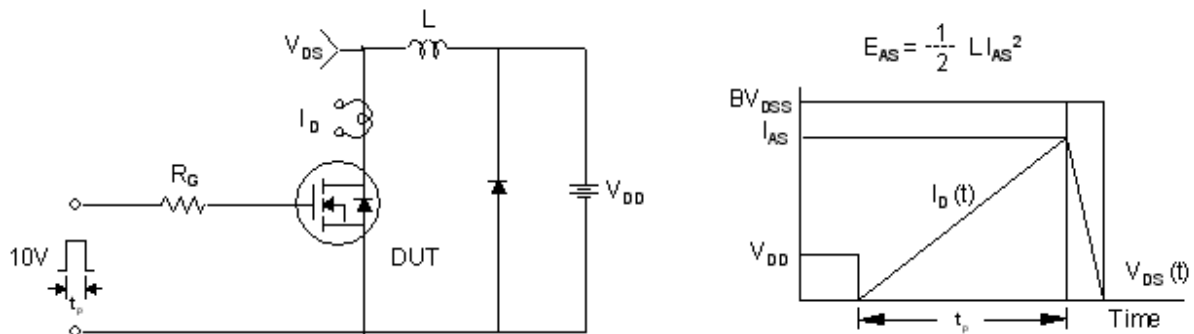
**Gate Charge Test Circuit & Waveform**



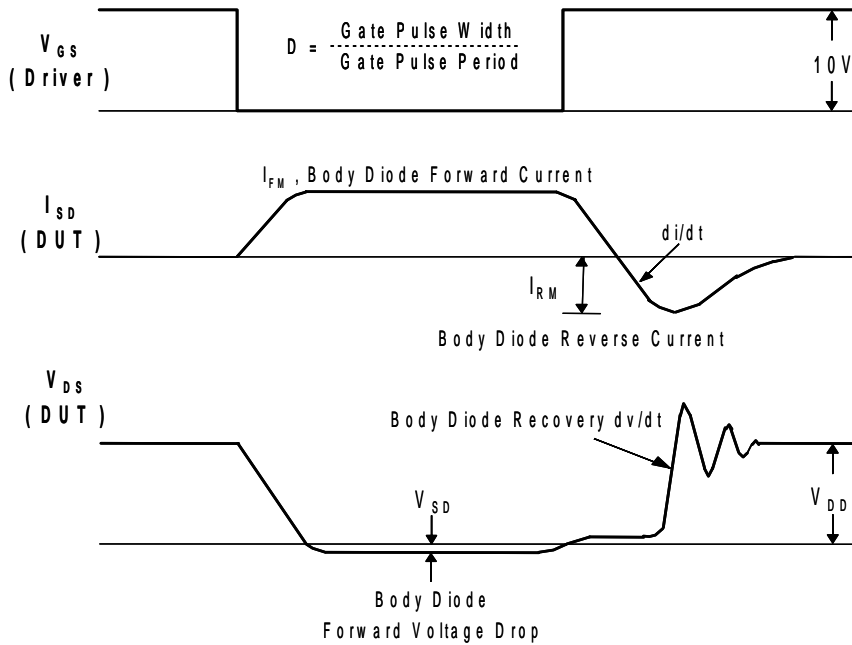
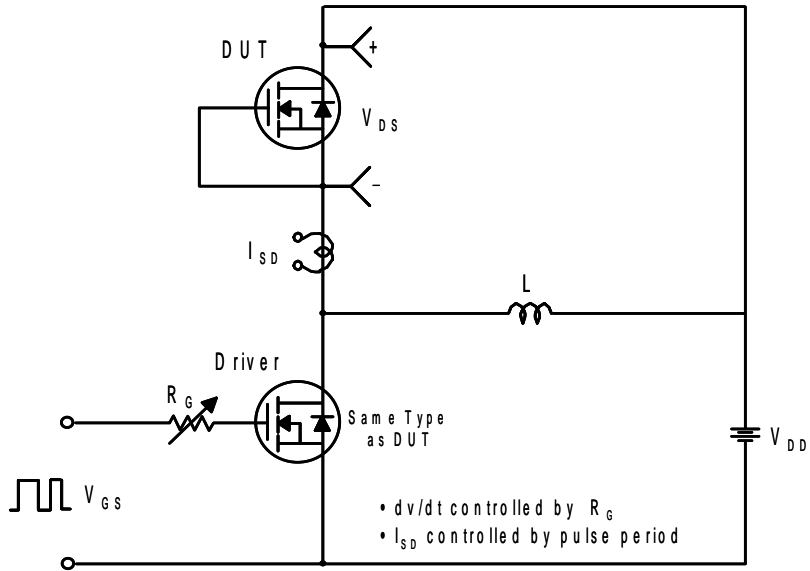
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

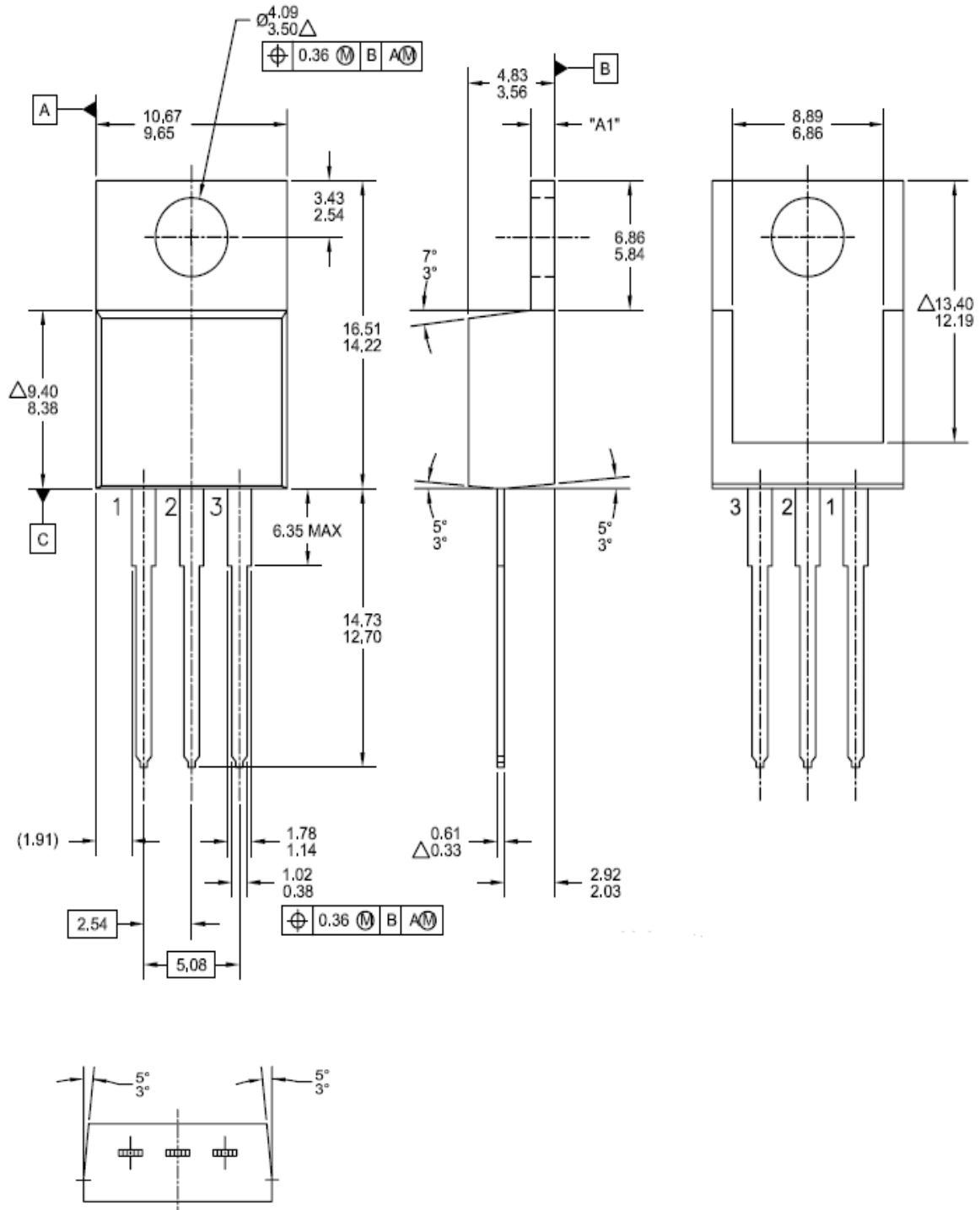


Peak Diode Recovery dv/dt Test Circuit & Waveforms



**Mechanical Dimensions**

**TO - 220**

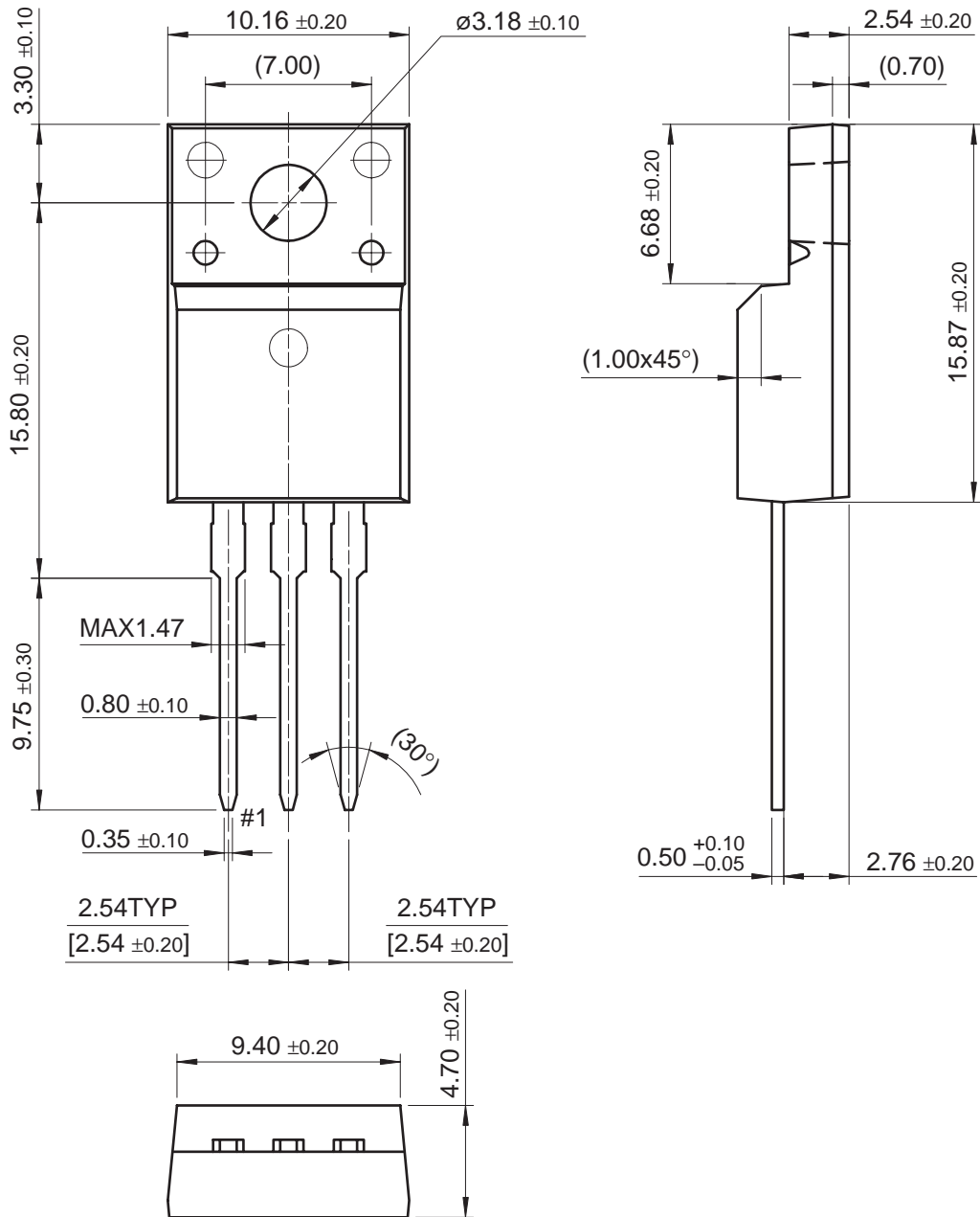


Dimensions in Millimeters



Mechanical Dimensions

TO-220F



Dimensions in Millimeters



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